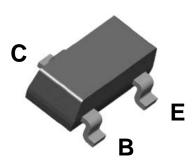


June 2007

BSR17A

NPN General Purpose Amplifier



SOT-23 MARK: U92

Features

This device is designed as a general purpose amplifier and switch.

The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier. Sourced from Process 23.

Absolute Maximum Ratings *Ta = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|---------------------------|--------------------|-------|
| V _{CBO} | Collector-Base Voltage | 60 | V |
| V_{CEO} | Collector-Emitter Voltage | 40 | V |
| V_{EBO} | Emitter-Base Voltage | 6.0 | V |
| I _C | Collector Current (DC) | 200 | mA |
| TJ | Junction Temperature | -55 ~ +150 | °C |
| T _{STG} | Storage Temperature | -55 ~ + 150 | °C |

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

Thermal Characteristics ${}^*T_a = 25^{\circ}C$ unless otherwise noted

| Symbol | Characteristic | Max | Units |
|---------------|---|-----|-------|
| Po | Total Device Dissipation | 350 | mW |
| | Derate above 25°C | 2.8 | mW/°C |
| R Θ JA | Thermal Resistance, Junction to Ambient | 357 | °C/W |

^{*}Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics *T_a = 25°C unless otherwise noted

| Parameter | Test Condition | MIN | MAX | Units |
|-------------------------------------|---|---|--|---|
| cteristics | | · | • | |
| Collector-Emitter Breakdown Voltage | Ic = 1.0 mA, IB = 0 | 40 | | V |
| Collector-Base Breakdown Voltage | Ic = 10 μA, Iв = 0 | 60 | | V |
| Emitter-Base Breakdown Voltage | Ic = 10 μA, Iв = 0 | 6.0 | | V |
| Collector-Cutoff Current | Vcb = 30 V, TA = 150°C | | 5.0 | μΑ |
| Emitter-Cutoff Current | VCE = 30 V, VEB = 3.0 V | | 50 | nA |
| IBEX Reverse Base Current | VCE = 30 V, VEB = 3.0 V | | 50 | nA |
| | Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Cutoff Current Emitter-Cutoff Current | Collector-Emitter Breakdown Voltage Ic = 1.0 mA, IB = 0 | Ceteristics Collector-Emitter Breakdown Voltage Ic = 1.0 mA, Iв = 0 40 Collector-Base Breakdown Voltage Ic = 10 μA, Iв = 0 60 Emitter-Base Breakdown Voltage Ic = 10 μA, Iв = 0 6.0 Collector-Cutoff Current VcB = 30 V, TA = 150°C Emitter-Cutoff Current VcE = 30 V, VeB = 3.0 V | Ceteristics Collector-Emitter Breakdown Voltage Ic = 1.0 mA, I _B = 0 40 Collector-Base Breakdown Voltage Ic = 10 μA, I _B = 0 60 Emitter-Base Breakdown Voltage Ic = 10 μA, I _B = 0 6.0 Collector-Cutoff Current V _{CB} = 30 V, T _A = 150°C 5.0 Emitter-Cutoff Current V _{CE} = 30 V, V _{EB} = 3.0 V 50 |

On Characteristics

| hfE | DC Current Gain | Ic = 0.1 mA, VcE = 1.0 V Ic = 1.0 mA, VcE = 1.0 V Ic = 10 mA, VcE = 1.0 V Ic = 50 mA, VcE = 1.0 V Ic = 100 mA, VcE = 1.0 V | 40 70 100 60 30 | 300 | |
|-----------------------|--|--|-----------------------------|--------------|--------|
| VCE(sat) | Collector-Emitter Saturation Voltage * | Ic = 10 mA, I _B = 1.0 mA Ic = 50 mA, I _B = 5.0 mA | | 0.2 0.3 | V V |
| V _{BE} (sat) | Emitter-Base Breakdown Voltage * | Ic = 10 mA, I _B = 1.0 mA Ic = 50 mA, I _B = 5.0 mA | 0.65 | 0.85 0.95 | V V |

Small Signal Characteristics

| f⊤ | Transition Frequency | Ic = 20 mA, VcE = 20 V, f = 100 MHz | 300 | | MHz |
|-----|----------------------------|--|-----|-----|-----|
| Ccb | Collector-Base Capacitance | VcB = 0.5 V, IE = 0, f = 1.0 MHz | | 4.0 | pF |
| Ceb | Emitter-Base Capacitance | V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz | | 8.0 | pF |
| hie | Input Impedance | VcE= 10 V,lc= 1.0 mA,f=1.0 kHz | 1.0 | 10 | kΩ |
| hfe | Small-Signal Current Gain | VcE= 10 V,lc= 1.0 mA,f=1.0 kHz | 100 | 400 | |
| hoe | Output Admittance | VcE= 10 V,Ic= 1.0 mA,f=1.0 kHz | 1.0 | 40 | μS |

Switching Characteristics

| td | Delay Time | Ic = 10 mA, I _B 1 = 1.0 mA,V _{EB} = 0.5 V | 35 | ns |
|----|--------------|---|-----|----|
| tr | Rise Time | | 4.0 | pF |
| ts | Storage Time | Ic = 10 mA, IBon = IBoff = 1.0 mA | 200 | ns |
| tf | Fall Time | | 50 | ns |

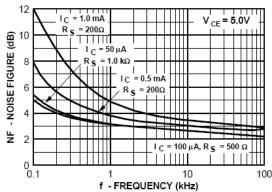
^{*}Pulse Test: Pulse Width 300 s, Duty Cycle 2.0 %

Spice Model

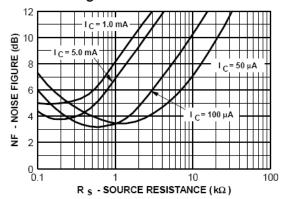
NPN (Is=6.734f Xti=3 Eg=1.11 Vaf=74.03 Bf=416.4 Ne=1.259 Ise=6.734 Ikf=66.78m Xtb=1.5 Br=.7371 Nc=2 Isc=0 Ikr=0 Rc=1 Cjc=3.638p Mjc=.3085 Vjc=.75 Fc=.5 Cje=4.493p Mje=.2593 Vje=.75 Tr=239.5n Tf=301.2p Itf=.4 Vtf=4 Xtf=2 Rb=10)

Typical Performance Characteristics

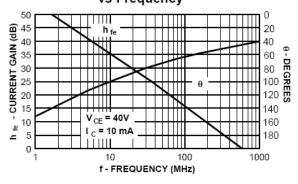
Noise Figure vs Frequency



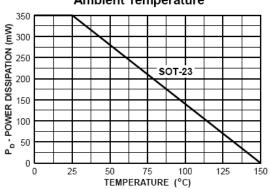
Noise Figure vs Source Resistance



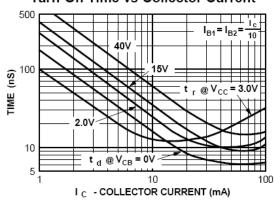
Current Gain and Phase Angle vs Frequency



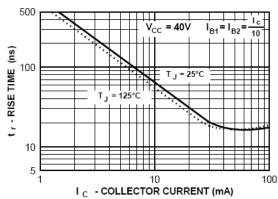
Power Dissipation vs Ambient Temperature



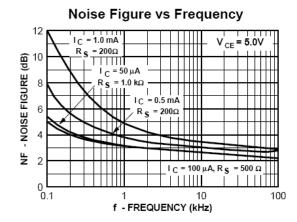
Turn-On Time vs Collector Current

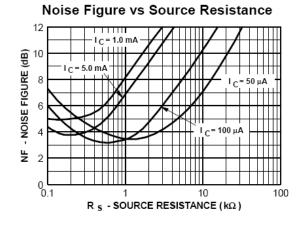


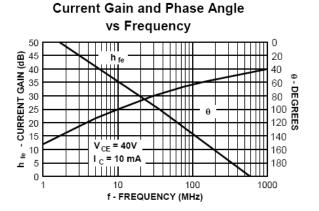
Rise Time vs Collector Current

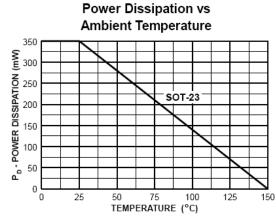


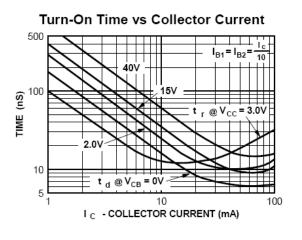
Typical Performance Characteristics (continued)

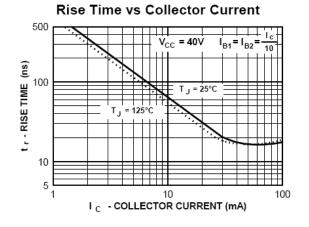






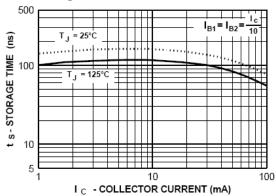




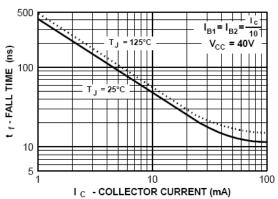


Typical Performance Characteristics (continued)

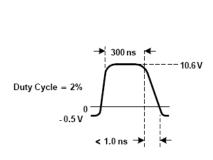
Storage Time vs Collector Current



Fall Time vs Collector Current



Test Circuits



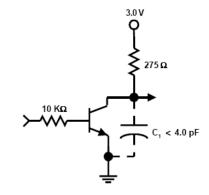
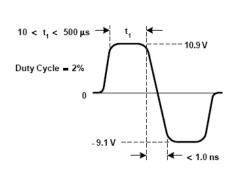


FIGURE 1: Delay and Rise Time Equivalent Test Circuit



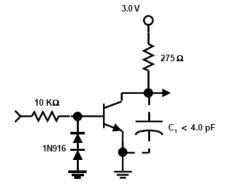


FIGURE 2: Storage and Fall Time Equivalent Test Circuit





UniFET™

 VCX^{TM}

Wire™

FAIRCHILD SEMICONDUCTOR TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

 OCX^{TM} SILENT SWITCHER® ACEx™ FACT Quiet Series™ OCXPro™ ActiveArray™ GlobalOptoisolator™ SMART START™ OPTOLOGIC® GTO™ SPM™ Bottomless™ OPTOPLANAR™ HiSeC™ Stealth™ Build it Now™ I^2C^{TM} PACMAN™ SuperFET™ CoolFET™ РОР™ i-LoTM CROSSVOLT™ SuperSOT™-3 Power247™ SuperSOT™-6 **DOME™** ImpliedDisconnect™ EcoSPARK™ PowerEdge™ IntelliMAX™ SuperSOT™-8 PowerSaver™ E²CMOS™ ISOPLANAR™ SyncFET™ PowerTrench® TCM^TM EnSigna™ LittleFET™ QFET® FACT[®] $\mathsf{MICROCOUPLER}^{\mathsf{TM}}$ TinyBoost™ TinyBuck™ FAST[®] QSTM MicroFET™ FASTr™ QT Optoelectronics™ TinyPWM™ MicroPak™ FPS™ Quiet Series™ MICROWIRE™ TinyPower™ FRFET™ MSXTM RapidConfigure™ TinyLogic[®] RapidConnect™ TINYOPTO™ MSXPro™ սSerDes™ TruTranslation™ Across the board. Around the world.™ ScalarPump™ **UHC®**

The Power Franchise®

Programmable Active Droop™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPE-CIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

| Datasheet Identification | Product Status | Definition |
|--------------------------|------------------------|---|
| Advance Information | Formative or In Design | This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. |
| Preliminary | First Production | This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design. |
| No Identification Needed | Full Production | This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design. |
| Obsolete | Not In Production | This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only. |

Rev. I23

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor: BSR17A_D87Z